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### **PN3563**



## **NPN RF Amplifier**

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43. See PN918 for characteristics.

#### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	15	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	2.0	V
Ic	Collector Current - Continuous	50	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		PN3563	
P <sub>D</sub>	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

# NPN RF Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
				•	•
OFF CHA	RACTERISTICS				
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage*	$I_C = 3.0 \text{ mA}, I_B = 0$	15		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100  \mu A, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10  \mu A,  I_C = 0$	2.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, I_{E} = 0$ $V_{CB} = 15 \text{ V}, T_{A} = 150^{\circ}\text{C}$		0.05 5.0	μA nA
ON CHAR	ACTERISTICS*				
L.	DC Current Gain	1 00 4 1/ 40 1/	20	200	
h <sub>FE</sub>	DC Current Gain	$I_C = 8.0 \text{ mA}, V_{CE} = 10 \text{ V}$	20	200	
SMALL SI	IGNAL CHARACTERISTICS	, 0			l Mile
SMALL SI	1 - 5 - 5 - 5 - 5 - 5 - 5 - 5 - 5 - 5 -	$I_C = 8.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	600	1500	MHz
SMALL SI	IGNAL CHARACTERISTICS	$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$			MHz pF pF
SMALL SI	IGNAL CHARACTERISTICS  Current Gain - Bandwidth Product	$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100  MHz $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		1500	pF
SMALL SI f <sub>T</sub> C <sub>obo</sub>	IGNAL CHARACTERISTICS  Current Gain - Bandwidth Product  Output Capacitance	$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100  MHz $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$ $V_{CB} = 0, I_{E} = 0, f = 1.0 \text{ MHz}$		1500 1.7 3.0	pF pF
SMALL SI f <sub>T</sub> C <sub>obo</sub> C <sub>ibo</sub>	GNAL CHARACTERISTICS  Current Gain - Bandwidth Product  Output Capacitance  Input Capacitance	$\begin{split} I_C = 8.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f = 100 \text{ MHz} \\ V_{CB} = 10 \text{ V}, \ I_E = 0, \ f = 1.0 \text{ MHz} \\ V_{CB} = 0, \ I_E = 0, \ f = 1.0 \text{ MHz} \\ V_{BE} = 0.5 \text{ V}, \ I_C = 0, \ f = 140 \text{ MHz} \\ I_C = 8.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \end{split}$	600	1500 1.7 3.0 2.0	pF pF
SMALL SI  f <sub>T</sub> C <sub>obo</sub> C <sub>ibo</sub> h <sub>fe</sub> rb'C <sub>C</sub>	GNAL CHARACTERISTICS  Current Gain - Bandwidth Product  Output Capacitance  Input Capacitance  Small-Signal Current Gain	$\begin{split} I_C = 8.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f = 100 \text{ MHz} \\ V_{CB} = 10 \text{ V}, \ I_E = 0, \ f = 1.0 \text{ MHz} \\ V_{CB} = 0, \ I_E = 0, \ f = 1.0 \text{ MHz} \\ V_{BE} = 0.5 \text{ V}, \ I_C = 0, \ f = 140 \text{ MHz} \\ I_C = 8.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f = 1.0 \text{ MHz} \\ I_C = 8.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \end{split}$	600	1500 1.7 3.0 2.0 250	pF pF pF

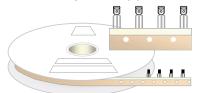
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

#### **TO-92 Tape and Reel Data** FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

#### TO-92 Tape and Reel Data, continued

# **TO-92 Reeling Style Configuration:** Figure 2.0

#### Machine Option "A" (H)

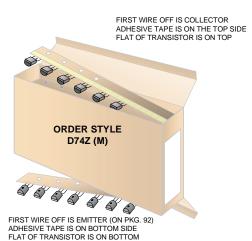


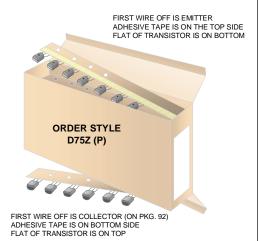
Style "A", D26Z, D70Z (s/h)

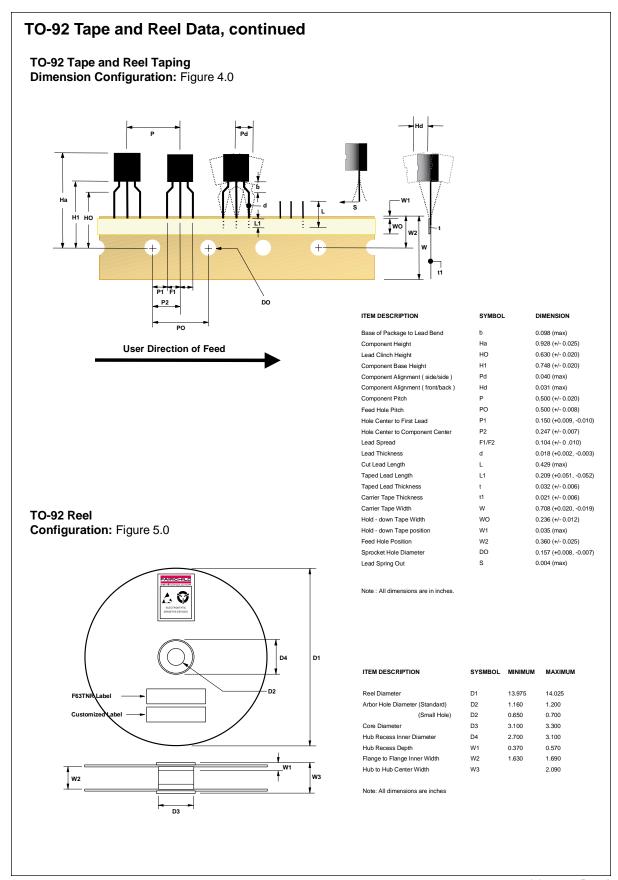
# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

# **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0



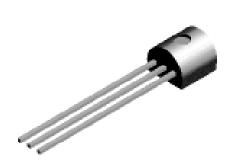


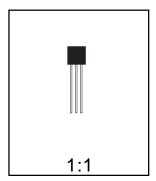


#### **TO-92 Package Dimensions**



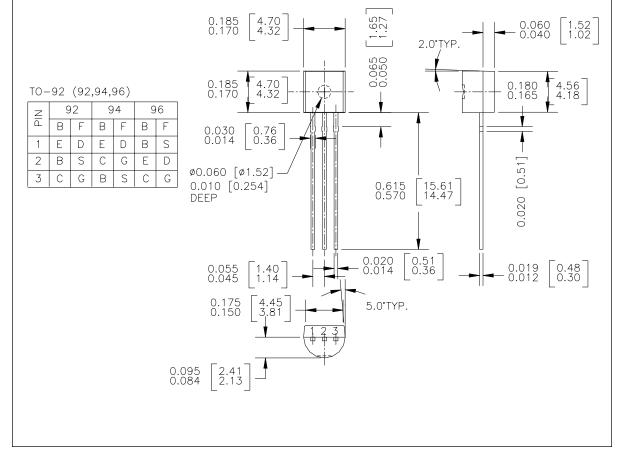
# TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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DOME™ ISOPLANAR™ Quiet Series™

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